

LED34-PR Mid-Infrared Light Emitting Diode

Description

The LED34-PR module is a light emitting diode designed with narrow band gap GaInAsSb/AlGaAsSb based heterostructures and manufactured with Metal-Organic Chemical Vapor Deposition (MOCVD) and liquid-phase epitaxy (LPE) technologies. It emits infrared (IR) radiation with center wavelength at 3400 nm.



Features

- Structure: GaInAsSb/AlGaAsSb
- Fast Response: <50 ns
- High Modulation: 100 MHz
- Package: TO-18 with a parabolic reflector without a window

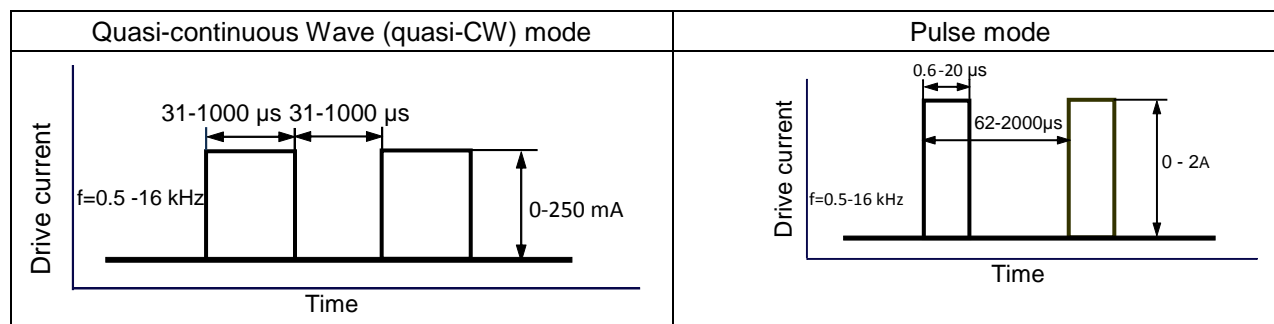
Applications

- Industrial Process Control
- Sensor development
- Medical diagnostics

Specification

Operation Mode

IR LED can be operated in Quasi Continuous Wave (qCW) mode or Pulse mode. qCW mode with duty cycle 50% or 25% is recommended to obtain maximum average optical power while short Pulse mode is recommended to obtain maximum peak power. Hard CW (continuous wave) mode is NOT recommended.

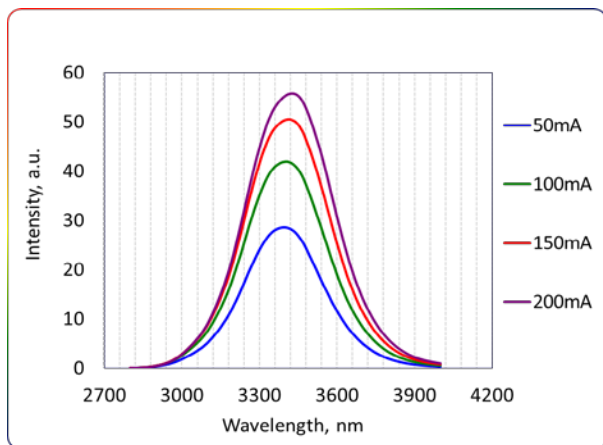


Optical and Electrical Characteristics

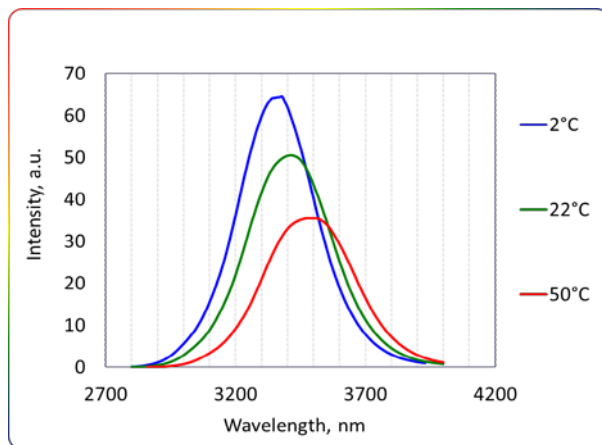
LED34-PR - Standard LED chip with circular or ring top contact					
Parameters	Units	Conditions	Ratings		
			Min	Typ	Max
Peak emission wavelength	μm	T=300 K, I = 150 mA qCW	3.30	3.40	3.49
FWHM of the emission band	nm	I = 150 mA qCW	400	500	600
Quasi-CW Optical Power	μW	I = 200 mA qCW	25.0	35.0	45.0
Pulsed Peak Optical Power	μW	I=1 A, f=1 kHz, duty cycle 0.1%	320	400	480
Voltage	V	T=300 K, I=200 mA	0.2	-	0.5
Switching time	ns	T=300 K	10	20	30
Operating temperature range	°C	-200 ~ +50			
Soldering temperature	°C	180			

Typical Characteristic Curves

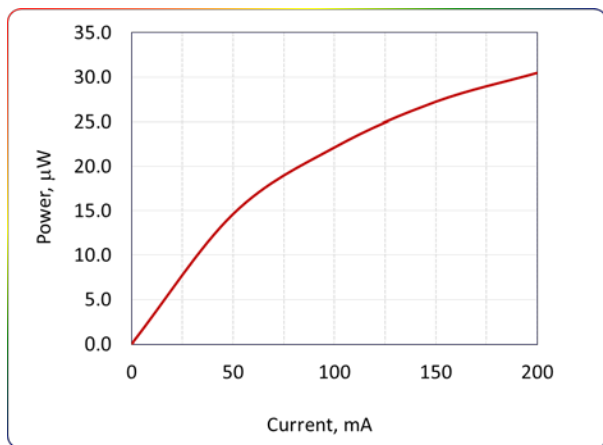
Spectra at different currents (qCW, T=300 K)



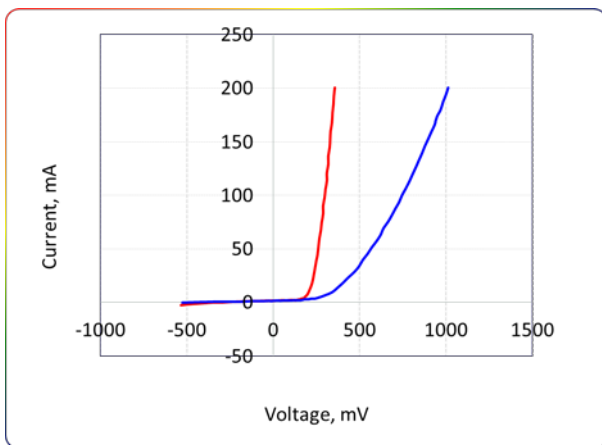
Spectra at different temperatures (qCW, I=150 mA)



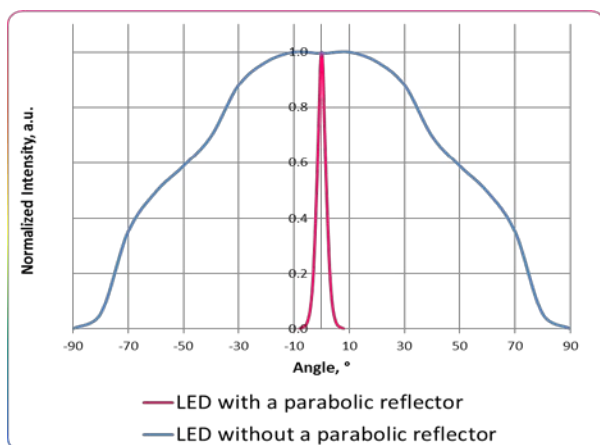
LED Power Characteristic (quasi-CW mode, T=300K)



LED Typical Current-Voltage Characteristics (T=300K)



Beam Divergence (Far-field pattern)



Note

LED polarity Mark
LED anode is marked with a **RED** dot.

